ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE116
General Purpose Silicon Rectifier

Description:

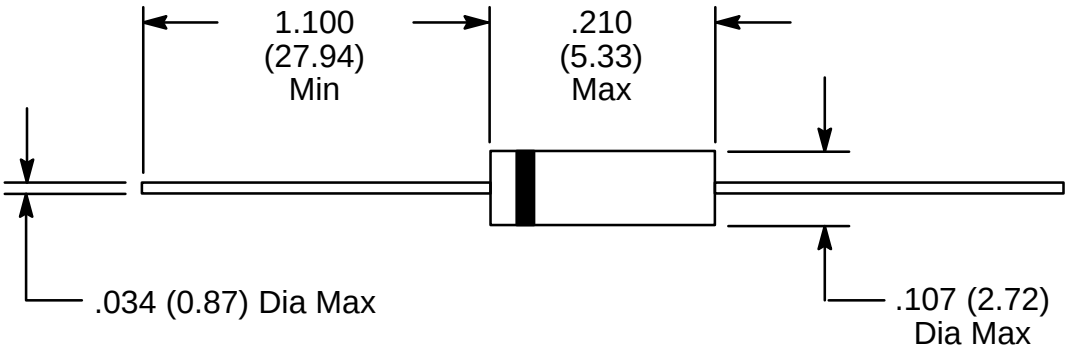
The NTE116 is a general purpose silicon rectifier in a DO–41 case designed for low power and switching applications.

Absolute Maximum Ratings:

Peak Repetitive Reverse Voltage, V_{RRM} 600V
Working Peak Reverse Voltage, V_{RWM} 600V
DC Blocking Voltage, V_R 600V
Non–Repetitive Peak Reverse Voltage (Halfwave, Single Phase, 60Hz), V_{RSM} 720V
RMS Reverse Voltage, $V_{R(RMS)}$ 420V
Average Rectified Forward Current. I_O
(Single Phase, Resistive Load, 60Hz, T_A = +75°C) 1A
Non–Repetitive Peak Surge Current, I_{FSM}
(Surge applied at rated load conditions for 1 cycle) 30A
Operating Junction Temperature Range, T_J . . . . . –65° to +175°C
Storage Temperature Range, T_{stg} . . . . . –65° to +175°C
Maximum Lead Temperature, T_L
(During Soldering, 3/8” from case for 10sec at 5lbs tension) . . . . . +350°C

Electrical Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage Drop	v_F	i_F = 1A, T_J = +25°C	–	0.93	1.1	V
Maximum Full–Cycle Average Forward Voltage Drop	$V_{F(AV)}$	I_O = 1A, T_L +75°C, 1” leads	–	–	0.8	V
Maximum Reverse Current	I_R	V_{RRM} = 600V, T_J = +25°C	–	0.05	10	µA
		V_{RRM} = 600V, T_J = +100°C	–	1.0	50	
Maximum Full–Cycle Average Reverse Current	$I_{R(AV)}$	I_O = 1A, T_L +75°C, 1” leads	–	–	30	µA



Color Band Denotes Cathode